

## Trimethylarsonium iodide

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## Key indicators

Single-crystal X-ray study  
 $T = 292$  K  
Mean  $\sigma(\text{s-C}) = 0.007$  Å  
 $R$  factor = 0.029  
 $wR$  factor = 0.078  
Data-to-parameter ratio = 22.4For details of how these key indicators were  
automatically derived from the article, see  
<http://journals.iucr.org/e>.

The title compound,  $\text{C}_3\text{H}_{10}\text{As}^+\text{I}^-$ , contains discrete  $[(\text{CH}_3)_3\text{AsH}]^+$  cations with a distorted tetrahedral geometry for the central As atom, which lies on a mirror plane. Weak van der Waals contacts are observed between the I atom and the H atoms in the range 3.15 (1)–3.25 (1) Å.

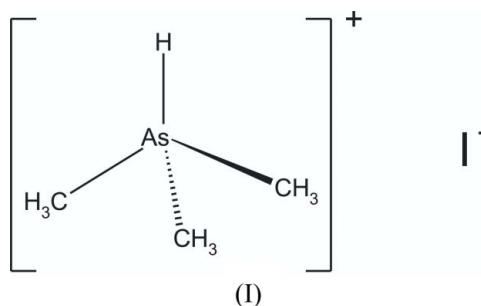
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## Comment

$[(\text{CH}_3)_4\text{As}]^+$  cations have been reported with a variety of different counteranions. Tetramethylarsonium halides, for example, have been characterized by X-ray structural analysis for the heavier halides bromide (Collins *et al.*, 1963) and iodide (Assenmacher & Jansen, 1995), whereas the chloride compound has not yet been characterized by single-crystal structure analysis, although Debye–Scherrer investigations have revealed that it is isostructural with  $(\text{CH}_3)_4\text{AsBr}$  (Ang & Dunell, 1976). In contrast, the trimethylarsonium cation has been characterized only twice. In both  $[(\text{CH}_3)_3\text{AsH}][\text{As}_2\text{F}_{11}]$  and  $[(\text{CH}_3)_3\text{AsH}][\text{SbF}_6]$  (Minkwitz *et al.*, 1999), relatively large counteranions are needed to stabilize the  $[(\text{CH}_3)_3\text{AsH}]^+$  cations in the solid state.



The title compound,  $(\text{CH}_3)_3\text{AsHI}$ , (I), is the first example of a discrete trimethylarsonium cation crystallizing with a halide counteranion. The As atom, which lies on a mirror plane, exhibits a distorted tetrahedral environment, with As–C distances of 1.923 (5) and 1.927 (8) Å, which are similar to those observed in  $[(\text{CH}_3)_3\text{AsH}][\text{As}_2\text{F}_{11}]$  [1.894 (5)–1.908 (5) Å].

The  $\text{I}^-$  counteranion exhibits long-range van der Waals interactions with its surrounding H atoms [ $\text{I} \cdots \text{H}$  3.15 (1)–3.25 (1) Å]; these stabilize the arrangement of (I) in the crystal packing (Fig. 2).

## Experimental

$\text{GeI}_4$  (580.19, 1.0 mmol),  $\text{As}_2\text{Se}_3$  (193.4 mg, 0.5 mmol), Se (79.0 mg, 1.0 mmol) and  $\text{K}_2\text{CO}_3$  (138.2 mg, 1.0 mmol) were heated to 433 K in  $\text{CH}_3\text{OH}$  (0.8 ml) in a sealed glass tube. After 2 d, the contents were

cooled to room temperature to afford colourless crystals of (I) in 52% yield.

Crystal data

$C_3H_{10}As^+I^-$   
 $M_r = 247.93$   
 Orthorhombic,  $Pnma$   
 $a = 14.174 (3) \text{ \AA}$   
 $b = 8.0458 (16) \text{ \AA}$   
 $c = 6.2037 (12) \text{ \AA}$   
 $V = 707.5 (2) \text{ \AA}^3$   
 $Z = 4$   
 $D_x = 2.328 \text{ Mg m}^{-3}$

Mo  $K\alpha$  radiation  
 Cell parameters from 21 reflections  
 $\theta = 6.2\text{--}15.0^\circ$   
 $\mu = 9.04 \text{ mm}^{-1}$   
 $T = 292 (2) \text{ K}$   
 Block, colourless  
 $0.41 \times 0.33 \times 0.21 \text{ mm}$

Data collection

Siemens P4 four-circle diffractometer  
 $\omega$  scans  
 Absorption correction:  $\psi$  scan (XPREP in SHELXTL; Sheldrick, 1995)  
 $T_{\min} = 0.040$ ,  $T_{\max} = 0.152$   
 671 measured reflections  
 671 independent reflections

576 reflections with  $I > 2\sigma(I)$   
 $\theta_{\max} = 25.0^\circ$   
 $h = 0 \rightarrow 16$   
 $k = -9 \rightarrow 3$   
 $l = 0 \rightarrow 7$   
 3 standard reflections every 97 reflections  
 intensity decay: none

Refinement

Refinement on  $F^2$   
 $R[F^2 > 2\sigma(F^2)] = 0.029$   
 $wR(F^2) = 0.078$   
 $S = 1.16$   
 671 reflections  
 30 parameters  
 H-atom parameters constrained

$w = 1/[\sigma^2(F_o^2) + (0.0439P)^2]$   
 where  $P = (F_o^2 + 2F_c^2)/3$   
 $(\Delta/\sigma)_{\max} < 0.001$   
 $\Delta\rho_{\max} = 0.82 \text{ e \AA}^{-3}$   
 $\Delta\rho_{\min} = -0.73 \text{ e \AA}^{-3}$   
 Extinction correction: SHELXL97 (Sheldrick, 1997)  
 Extinction coefficient: 0.0286 (17)

Table 1

Selected geometric parameters ( $\text{\AA}$ ,  $^\circ$ ).

As—C1	1.923 (6)	As—C2	1.927 (8)
$C1^i$ —As—C1	98.9 (3)	C1—As—C2	97.8 (2)

Symmetry code: (i)  $x, -y + \frac{1}{2}, z$ .

H atoms were located in a difference electron-density map but were refined with fixed individual displacement parameters [ $U_{\text{iso}}(\text{H}) = 1.5U_{\text{eq}}(\text{C})$ ] using a riding model, with C—H = 0.96  $\text{\AA}$ . The idealized As—H bond length is 1.40  $\text{\AA}$ .

Data collection:  $R3m/V$  (Siemens, 1989); cell refinement:  $R3m/V$ ; data reduction: XDISK (Siemens, 1989); program(s) used to solve structure: SHELXS97 (Sheldrick, 1997); program(s) used to refine structure: SHELXL97 (Sheldrick, 1997); molecular graphics: SHELXTL (Sheldrick, 1995); software used to prepare material for publication: SHELXL97.

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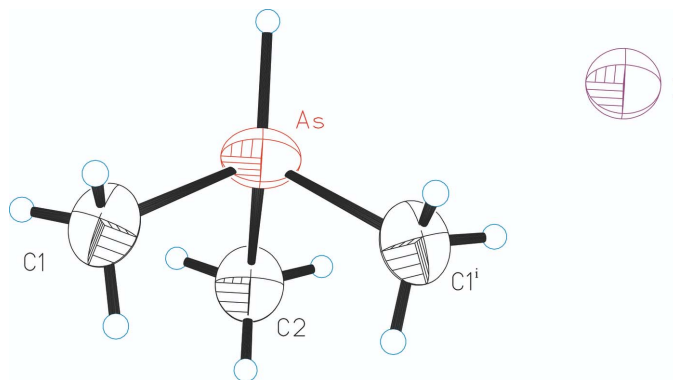


Figure 1

The structure of (I). Displacement ellipsoids are drawn at the 50% probability level. [Symmetry code: (i)  $x, \frac{1}{2} - y, z$ ]

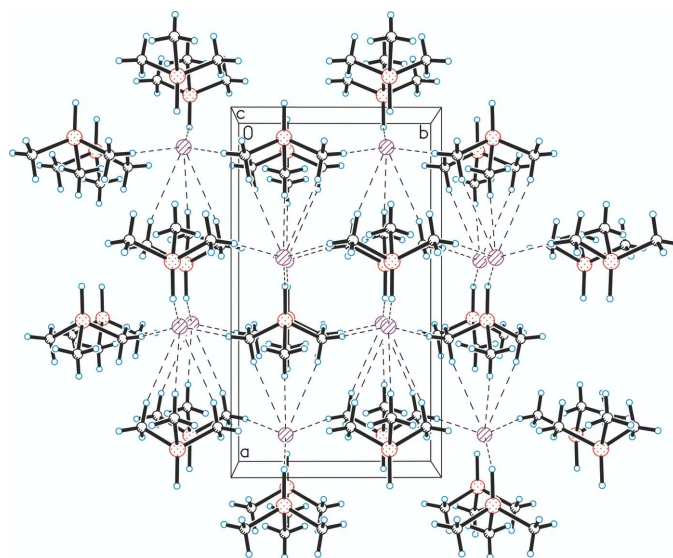


Figure 2

Projection of the structure of (I) perpendicular to the  $ab$  plane, showing the weak van der Waals interactions (dashed lines) of the I atoms. Atom colour codes: I purple, As red, C black and H blue.

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